ROLE OF THE ELECTRON-DEFORMATION INTERACTION IN THE FORMATION OF THE $n - n^+$ JUNCTION IN A DOPED CRYSTAL MATRIX

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S u m m a r y

In the framework of the electron-deformation model, the criterion of the appearance and the absence of an $n - n^+$ junction in the elastic region of the doped crystal matrix GaAs(100)+Ar(Si) has been established. It has been shown that the more the population of the conduction band ($0 \leq \bar{n} \leq 0.5$), the sharper the $n - n^+$ junction. In this case, the plane corresponding to the junction edge shifts towards the edge of the elastic region.